NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$  and R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

Rev. 6 — 24 January 2012

**Product data sheet** 

### 1. Product profile

### 1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in small Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview
	TIOGUOL	

Type number	Package			
	NXP	JEITA	configuration	
PEMD48	SOT666	-	ultra small and flat lead	
PUMD48	SOT363	SC-88	very small	

### **1.2 Features and benefits**

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

### 1.4 Quick reference data

Table 2.	Quick reference data						
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
Per transistor; for the PNP transistor with negative polarity							
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V	
I <sub>O</sub>	output current		-	-	100	mA	
Transisto	r TR1 (NPN)						
R1	bias resistor 1 (input)		33	47	61	kΩ	
R2/R1	bias resistor ratio		0.8	1.0	1.2		
Transistor TR2 (PNP)							
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ	
R2/R1	bias resistor ratio		17	21	26		



#### **NPN/PNP** resistor-equipped transistors

## 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
PEMD48	(SOT666)		
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2	0	
5	input (base) TR2		
6	output (collector) TR1	1 2 3	

PUMD4	18 (SOT363)		
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2	□1 □2 □3	
6	output (collector) TR1		

## 3. Ordering information

Table 4. Ordering information					
Type number	Package				
	Name	Description	Version		
PEMD48	-	plastic surface-mounted package; 6 leads	SOT666		
PUMD48	SC-88	plastic surface-mounted package; 6 leads	SOT363		

### 4. Marking

Marking code <sup>[1]</sup>
48
4*8

[1] \* = placeholder for manufacturing site code.

PEMD48\_PUMD48
Product data sheet

2 3 006aaa143

2 3 006aaa143

**NPN/PNP** resistor-equipped transistors

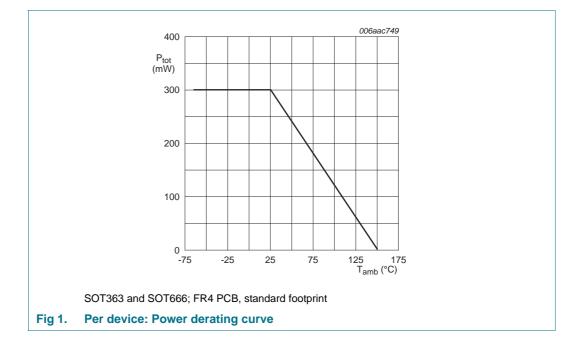
## 5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	with negative pola	rity		
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector			
	TR1 (NPN)		-	10	V
	TR2 (PNP)		-	-5	V
VI	input voltage TR1				
	positive		-	+40	V
	negative		-	-10	V
	input voltage TR2				
	positive		-	+5	V
	negative		-	-12	V
lo	output current		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMD48 (SOT666)		<u>[1][2]</u> _	200	mW
	PUMD48 (SOT363)		<u>[1]</u> -	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMD48 (SOT666)		[1][2] _	300	mW
	PUMD48 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

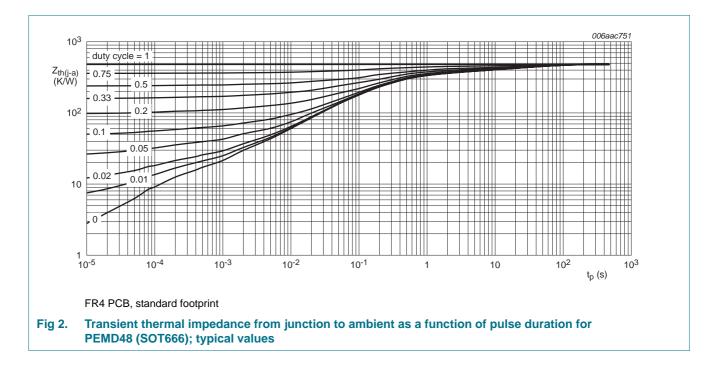
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

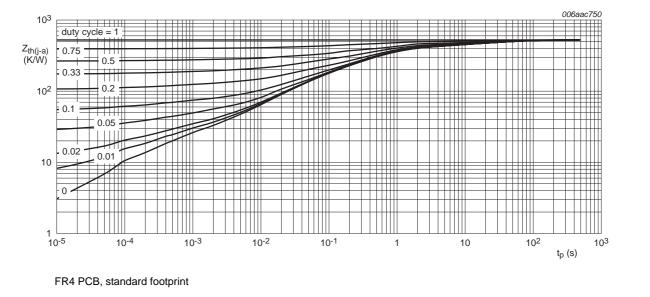
#### **NPN/PNP** resistor-equipped transistors



### 6. Thermal characteristics



#### **NPN/PNP** resistor-equipped transistors





• • •	<b>B</b>	<b>A</b> 11/1		-		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	PEMD48 (SOT666)		[1][2]	-	625	K/W
	PUMD48 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device	)					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^\circ C$				
	PEMD48 (SOT666)		[1][2] _	-	417	K/W
	PUMD48 (SOT363)		<u>[1]</u> _	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

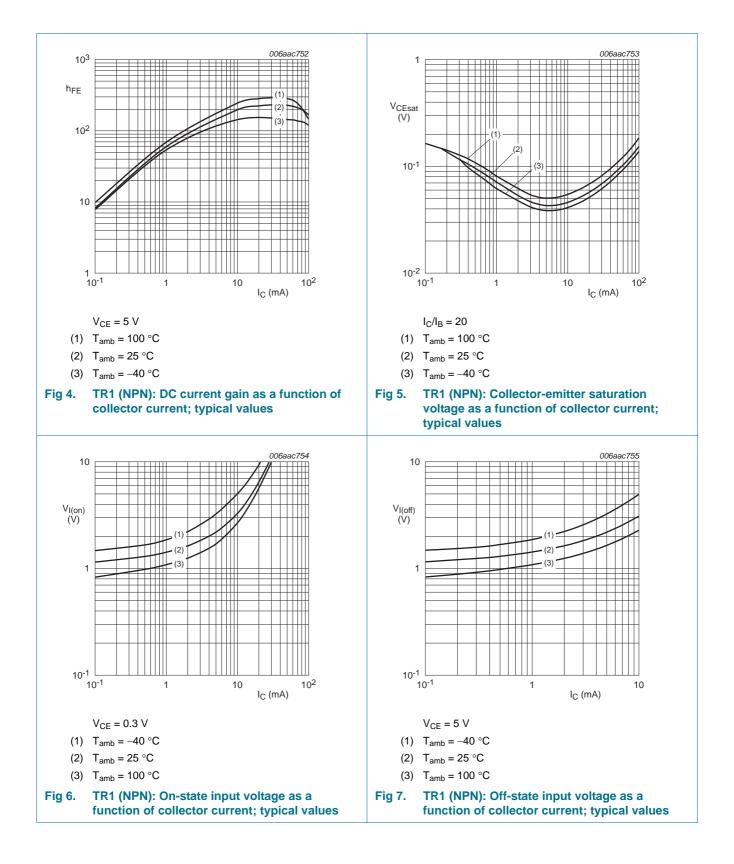
NPN/PNP resistor-equipped transistors

## 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	istor; for the PNP trans	istor with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$		-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$		-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A};$ T <sub>j</sub> = 150 °C		-	-	5	μΑ
Transisto	or TR1 (NPN)						
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$		-	-	90	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$		80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 10 mA; $I_{B}$ = 0.5 mA		-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = 5 V; $I_{C}$ = 100 $\mu$ A		-	1.2	0.8	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$		3	1.6	-	V
R1	bias resistor 1 (input)			33	47	61	kΩ
R2/R1	bias resistor ratio			0.8	1.0	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_E$ = $i_e$ = 0 A; f = 1 MHz		-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CB} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	<u>[1]</u>	-	230	-	MHz
Transisto	r TR2 (PNP)						
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -10 \text{ mA}$		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -5 mA; $I_{B}$ = -0.25 mA		-	-	-100	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = –5 V; $I_{C}$ = –100 $\mu A$		-	-0.6	-0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE}$ = –0.3 V; $I_{C}$ = –5 mA		-1.1	-0.75	-	V
R1	bias resistor 1 (input)			1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio			17	21	26	
C <sub>c</sub>	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$		-	-	3	pF
f <sub>T</sub>	transition frequency	V <sub>CB</sub> = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz	<u>[1]</u>	-	180	-	MHz

[1] Characteristics of built-in transistor.

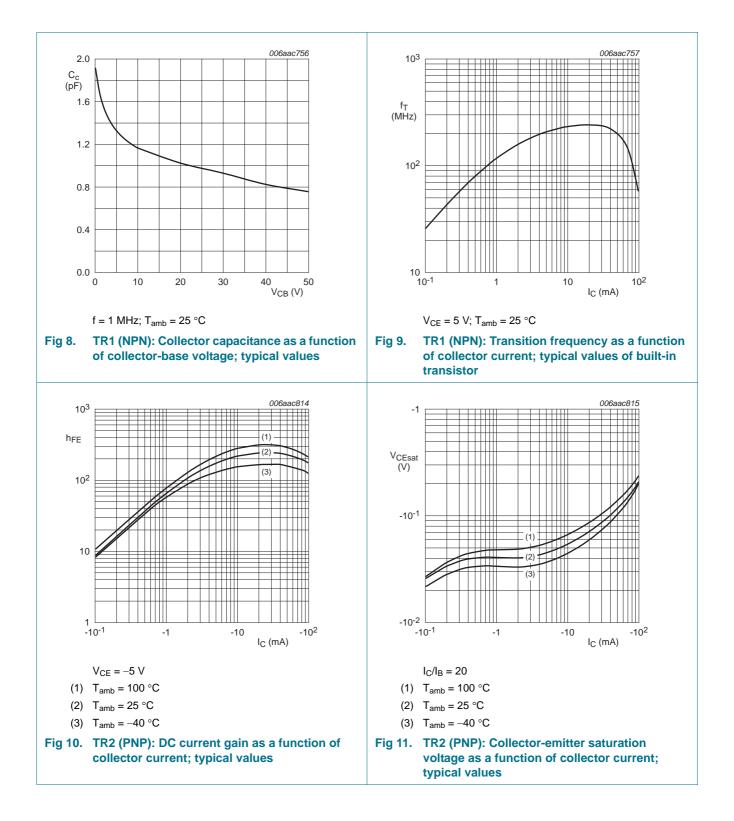
#### NPN/PNP resistor-equipped transistors



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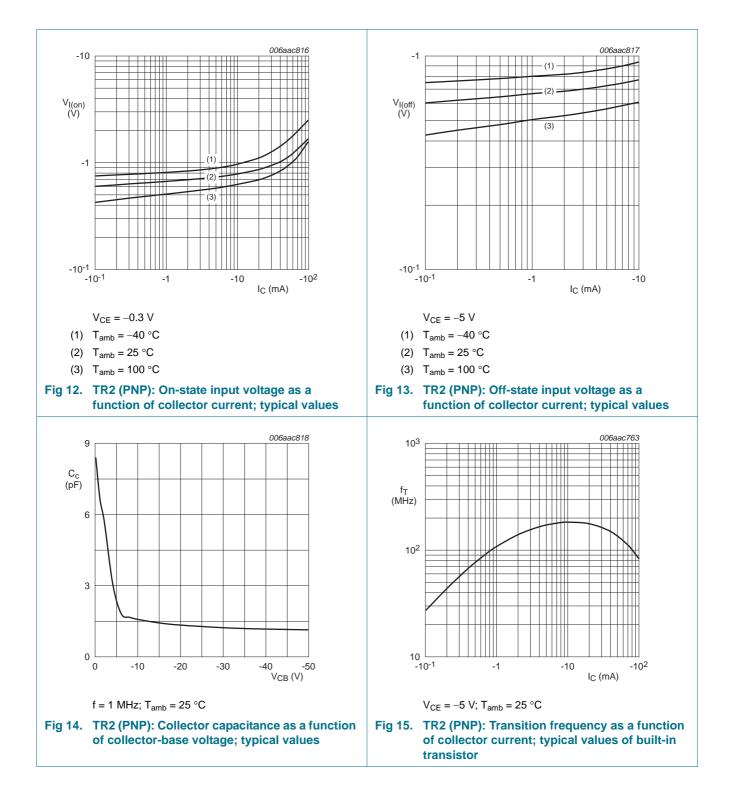
## PEMD48; PUMD48

#### NPN/PNP resistor-equipped transistors



PEMD48\_PUMD48
Product data sheet

#### NPN/PNP resistor-equipped transistors



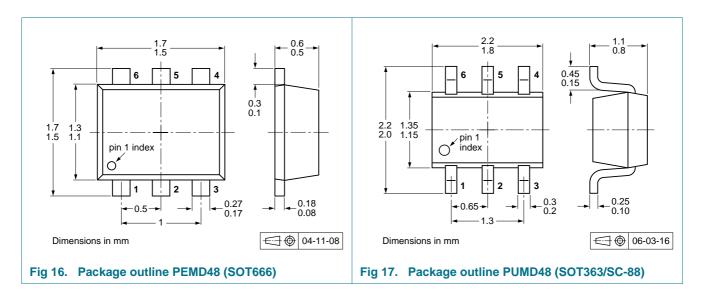
**NPN/PNP** resistor-equipped transistors

### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



NPN/PNP resistor-equipped transistors

### **10. Packing information**

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

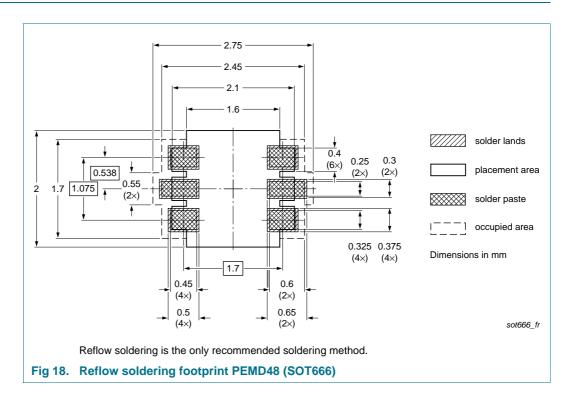
Туре	Package	Description		Packin	g quant	ity	
number				3000	4000	8000	10000
PEMD48	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMD48	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

[1] For further information and the availability of packing methods, see Section 14.

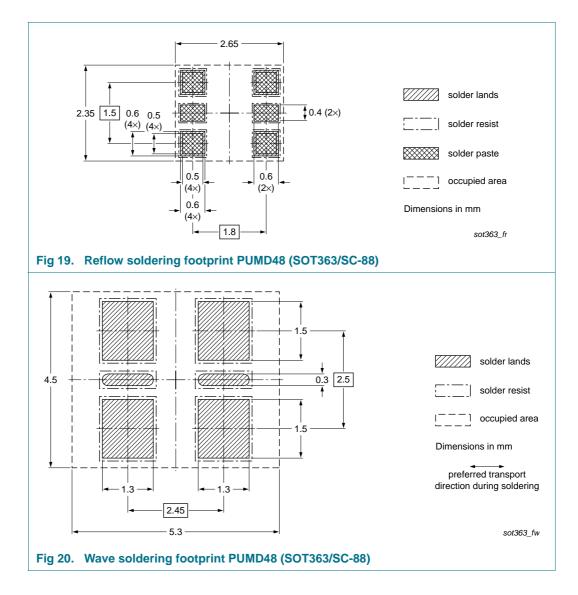
[2] T1: normal taping

[3] T2: reverse taping

## 11. Soldering



#### **NPN/PNP** resistor-equipped transistors



PEMD48\_PUMD48

### NPN/PNP resistor-equipped transistors

## 12. Revision history

#### Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD48_PUMD48 v.6	20120124	Product data sheet	-	PEMD48_PUMD48 v.5
Modifications:	Section 1 "Properties of the section of the sect	oduct profile": updated		
	<ul> <li>Section 4 "Ma</li> </ul>	rking": updated		
	• Table 7 "Ther	mal characteristics": upda	ted according to the la	test measurements
	• Table 6 "Limit	ing values": updated acco	ording to the latest mea	surements
	• Table 8 "Char	acteristics": ICEO updated	according to the latest	measurements, $f_T$ added
	<ul> <li>Figure 1 to 3,</li> </ul>	<u>8, 9, 14</u> and <u>15</u> : added		
	• Figure 4 to 7	and <u>Figure 10</u> to <u>13</u> : upda	ited	
	Section 8 "Tes	st information": added		
	Section 11 "Section 11 "Section 11"	oldering": added		
	Section 13 "Logistical and the section of the se	egal information": updated	Ł	
PEMD48_PUMD48 v.5	20100413	Product data sheet	-	PEMD48_PUMD48 v.4
PEMD48_PUMD48 v.4	20040624	Product specification	-	PEMD48_PUMD48 v.3
PEMD48_PUMD48 v.3	20040602	Product specification	-	PEMD48 v.2
				PUMD48 v.2
PUMD48 v.2	20010201	Product specification		PUMD48 v.1
PUMD48 v.1	19990422	Product specification		-
PEMD48 v.2	20011107	Product specification		PEMD48 v.1
PEMD48 v.1	20010924	Preliminary specification	on -	-

**NPN/PNP** resistor-equipped transistors

### 13. Legal information

### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMD48\_PUMD48

#### NPN/PNP resistor-equipped transistors

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#### **NPN/PNP** resistor-equipped transistors

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